

Appl. No. 10/010,548
Amdt. dated November 26, 2003
Reply to Office Action of August 29, 2003

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listing, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of etching a semiconductor device using a neutral beam comprising:
extracting an ion beam having a predetermined polarity from an ion source to accelerate the ion beam such that an incident angle of the ion beam is in a range of 75 - 85° from a vertical line to a horizontal surface of a reflector;
reflecting an accelerated ion beam by at the reflector to neutralize the reflected ion beam; and
positioning a substrate to be etched in a path of a neutral beam to etch a material layer on the substrate with the neutral beam.
- 2-3. (Canceled).
4. (Currently Amended) The method of claim 31, further comprising adjusting a gradient of the reflector to an incident ion beam.
5. (Currently Amended) The method of claim 31, further comprising applying a voltage to the reflector to adjust a path of an incident ion beam.
6. (Previously Presented) The method of claim 1, wherein the reflector is selected from the group consisting of a semiconductor substrate, a silicon dioxide substrate and a metal substrate.
- 7-17. (Canceled)